



DMN2230U

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

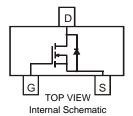
- Low On-Resistance
 - 110 m Ω @ $V_{GS} = 4.5V$
 - 145 m Ω @ $V_{GS} = 2.5V$
 - 230 m Ω @ $V_{GS} = 1.8V$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2, 3 and 5)
- Qualified to AEC-Q101 Standards for High Reliability



SOT-23

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±12	V
Drain Current (Note 1)	I _D	2.0	А
Pulsed Drain Current (Note 4)	I _{DM}	7	А

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P_{D}	600	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	208	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

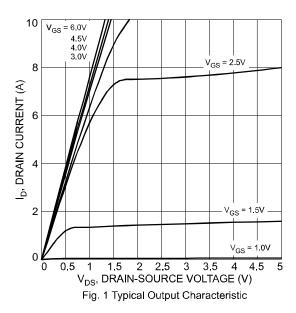
- 1. Device mounted on FR-4 PCB, or minimum recommended pad layout
- 2. No purposefully added lead. Halogen and Antimony Free.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Repetitive rating, pulse width limited by junction temperature.
 Product manufactured with Green Molding Compound and does not contain Halogens or Sb₂O₃ Fire Retardants.

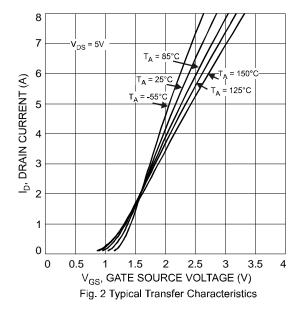


Electrical Characteristics @T_A = 25°C unless otherwise specified

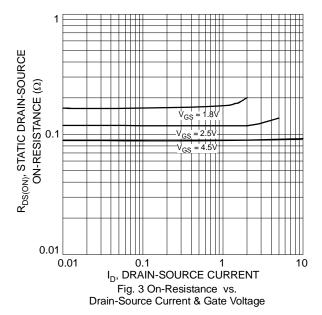
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	0.5		1.0	V	$V_{DS} = V_{CS}, I_D = 250 \mu A$	
	R _{DS} (ON)	_	81	110	mΩ	$V_{GS} = 4.5V, I_D = 2.5A$	
Static Drain-Source On-Resistance			113	145		V _{GS} = 2.5V, I _D = 1.5A	
			170	230		V _{GS} = 1.8V, I _D = 1.0A	
Forward Transfer Admittance	Y _{fs}	_	5	_	S	V _{DS} =5V, I _D = 2.4A	
Diode Forward Voltage (Note 6)	V _{SD}	_	0.8	1.1	V	V _{GS} = 0V, I _S = 1.05A	
DYNAMIC CHARACTERISTICS	•						
Input Capacitance	C _{iss}		188		рF	.,,	
Output Capacitance	Coss	_	44	_	pF	$V_{DS} = 10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	30	_	pF	1 - 1.00112	
Turn-On Delay Time	t _{d(on)}	_	8	_			
Rise Time	t _r	_	3.8	_	ns	$V_{DD} = 10V, R_L = 10\Omega$	
Turn-Off Delay Time	t _{d(off)}	_	19.6	_	118	$I_D = 1A, V_{GEN} = 4.5V, R_G = 6\Omega$	
Fall Time	t _f	_	8.3	_			

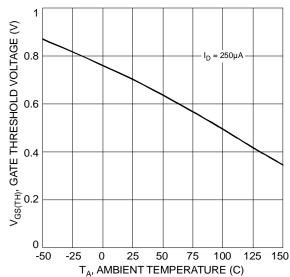
Notes: 6. Short duration pulse test used to minimize self-heating effect.

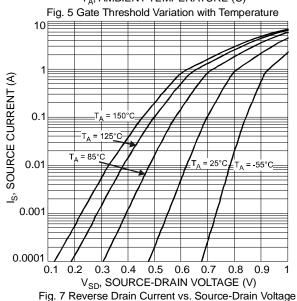












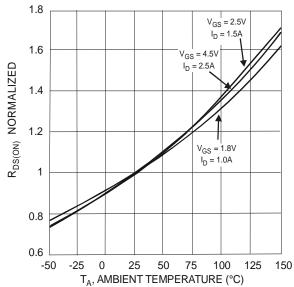
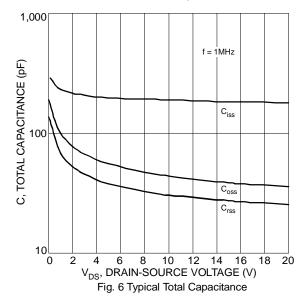


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature



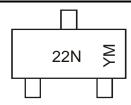


Ordering Information (Note 7)

Part Number	Case	Packaging
DMN2230U-7	SOT-23	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

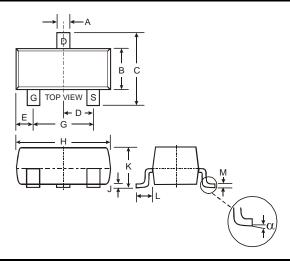


22N = Marking Code YM = Date Code Marking Y = Year ex: U = 2007 M = Month ex: 9 = September

Date Code Key (If Applicable)

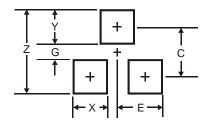
Year	20	07	20	08	20	09	20	10	20	11	20	12
Code	l	J	\	1	V	٧)	<	`	1	2	7
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89	1.03			
Е	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
M	0.085	0.180			
α	0°	8°			
All Dir	All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
G	0.7
Х	0.9
Y	1.4
C	2.0
Е	0.9

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